## This Page Is Inserted by IFW Operations and is not a part of the Official Record

## **BEST AVAILABLE IMAGES**

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

## IMAGES ARE BEST AVAILABLE COPY.

As rescanning documents will not correct images, please do not report the images to the Image Problem Mailbox.

## AMENDMENT TO THE CLAIMS

Please **AMEND** claims 1, 15 and 16 as shown below. Please **ADD** claim 18 as shown below The following is a listing of the claims in this application:

1. (Currently Amended) A method of reducing film growth rate when growing a carbonor boron-doped silicon film or silicon-germanium film, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases and a dopant profile can be spiked.

- 2. (Original) The method of Claim 1, including supplying germanium precursor to the substrate.
- 3. (Original) The method of Claim 1, wherein the film has a dopant content of about 1 x  $10^{17}$  to 1 x  $10^{21}$  / cm<sup>3</sup>.
- 4. (Original) The method of Claim 1, wherein the doping is at a temperature of less than 800°C.
- 5. (Previously presented) The method according to claim 1, wherein the dopant is carbon.
- 6. (Previously presented) The method according to claim 2, wherein the dopant is carbon.

- 7. (Previously presented) The method according to claim 6, wherein the carbon doping is by a carbon precursor supply that is a single source.
- 8. (Previously presented) The method according to claim 2, wherein the film has a germanium content of 1 to 30% by weight.
- 9. (Previously presented) The method according to Claim 1, wherein the silicon precursor is silane supplied at a partial pressure in a range of about 0.1 to 10 millitorr.
  - 10-14. (Withdrawn).
- 15. (Currently Amended) A method of growing a film without sharp pressure transitions, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduce pressure of about 0.1 to 100 millitorr, wherein a dopant profile of the carbon or boron-doping is spiked.

- 16. (Currently amended) The method of claim 45 18, wherein the step of carbon or boron-doping comprises carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, is provided at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.
- 17. (Previously presented) The method of claim 15, wherein the step of carbon or boron-doping comprises carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow

rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

18. (Added) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr,

wherein at least one of Si and SiGe films have spiked borders where dopant introduction of the carbon or boron-doping has been first introduced or stopped.